

P-Channel JFETs**Product Summary**

Part Number	V _{GS(off)} Max (V)	r _{D(on)} Max (Ω)	I _{D(off)} Typ (pA)	t _{ON} Typ (ns)
P1086	10	75	-10	25
P1087	5	150	-10	30

Features

- Low On-Resistance: P1086 <75 Ω
- Fast Switching—t_{ON}: 25 ns
- High Off-Isolation—I_{D(off)}: -10 pA
- Low Capacitance: 5 pF
- Low Insertion Loss

Benefits

- Low Error Voltage
- High-Speed Analog Circuit Performance
- Negligible “Off-Error,” Excellent Accuracy
- Good Frequency Response
- Eliminates Additional Buffering

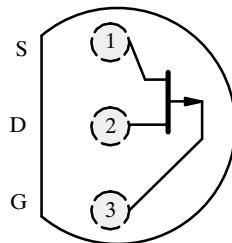
Applications

- Analog Switches
- Choppers
- Sample-and-Hold
- Normally “On” Switches
- Current Limiters

Description

The P1086/1087 are p-channel analog switches designed to provide low on-resistance and fast switching. These devices are optimized for use in complementary switching applications with the Siliconix J/SST111 series.

These devices are available in various lead forms and tape-and-reel for automated assembly (see Packaging Information).

TO-226AA
(TO-92)

Top View

Absolute Maximum Ratings

Gate-Drain Voltage	30 V
Gate-Source Voltage	30 V
Gate Current	-50 mA
Storage Temperature	-55 to 150°C
Operating Junction Temperature	-55 to 150°C

Lead Temperature (1/16" from case for 10 sec.) 300°C

Power Dissipation^a 350 mW

Notes

a. Derate 2.8 mW/°C above 25°C

P1086/1087

TEMIC

Siliconix

Specifications^a

Parameter	Symbol	Test Conditions	Typ ^b	Limits				Unit	
				P1086		P1087			
				Min	Max	Min	Max		
Static									
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = 1 μA, V _{DS} = 0 V	45	30		30		V	
Gate-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = -15 V, I _D = -1 μA			10		5		
Saturation Drain Current ^c	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V		-10		-5		mA	
Gate Reverse Current	I _{GSS}	V _{GS} = 15 V, V _{DS} = 0 V T _A = 85°C	0.01 0.6		2		2	nA	
Gate Operating Current	I _G	V _{DG} = -15 V, I _D = -1 mA	0.01						
Drain Cutoff Current	I _{D(off)}	V _{DS} = -15 V V _{GS} = 12 V V _{GS} = 7 V T _A = 85°C	-0.01 -0.01 -0.001		-10		-10	μA	
Drain-Source On-Resistance	r _{DS(on)}	V _{GS} = 0 V, I _D = -1 mA			75		150	Ω	
Gate-Source Forward Voltage	V _{GS(F)}	V _{DS} = 0 V, I _G = -1 mA	-0.7					V	
Dynamic									
Common-Source Forward Transconductance	g _{fs}	V _{DS} = -15 V, I _D = -1 mA f = 1 kHz	4.5					mS	
Common-Source Output Conductance	g _{os}		20					μS	
Drain-Source On-Resistance	r _{ds(on)}	V _{GS} = 0 V, I _D = 0 mA, f = 1 kHz			75		150	Ω	
Common-Source Input Capacitance	C _{iss}	V _{DS} = -15 V, V _{GS} = 0 V f = 1 MHz	20		45		45	pF	
Common-Source Reverse Transfer Capacitance	C _{rss}	V _{DS} = 0 V, V _{GS} = 10 V, f = 1 MHz	5		10		10		
Equivalent Input Noise Voltage	ē _n	V _{DG} = -10 V, I _D = -1 mA f = 1 kHz	20					nV/ √Hz	
Switching									
Turn-On Time	t _{d(on)}	V _{GS(L)} = 0 V, V _{GS(H)} = 10 V See Switching Circuit	10		15		15	ns	
	t _r		15		20		75		
Turn-Off Time	t _{d(off)}		10		15		25		
	t _f		20		50		100		

Notes

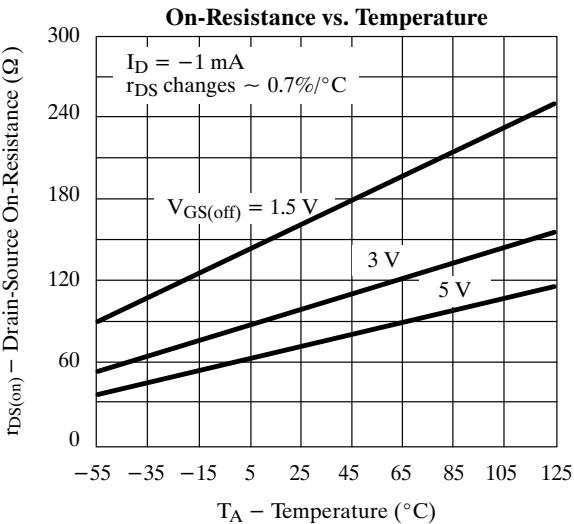
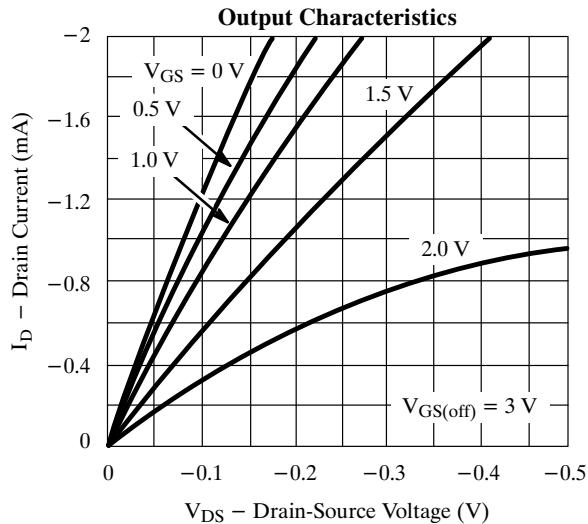
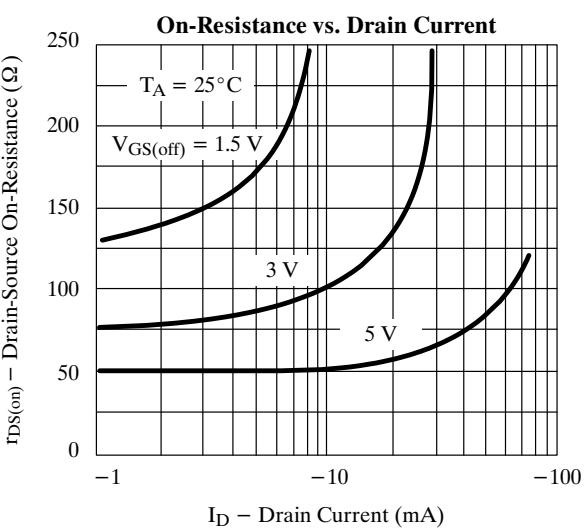
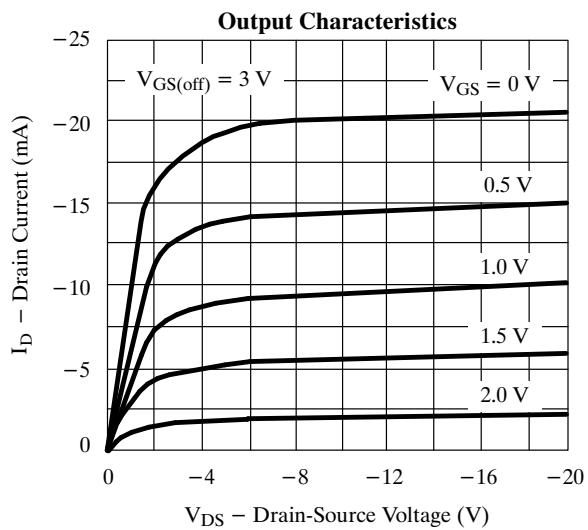
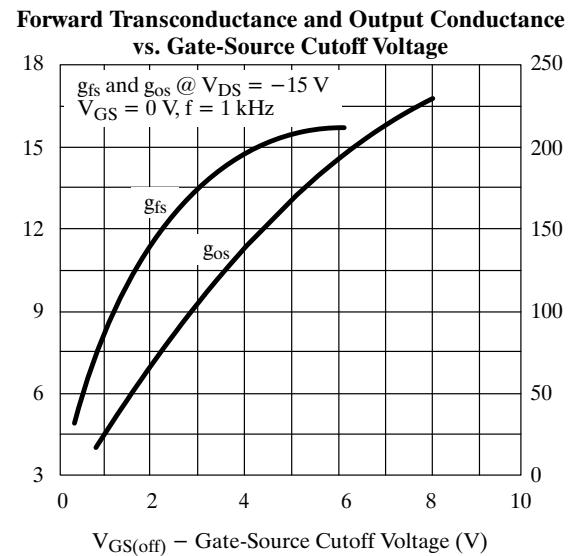
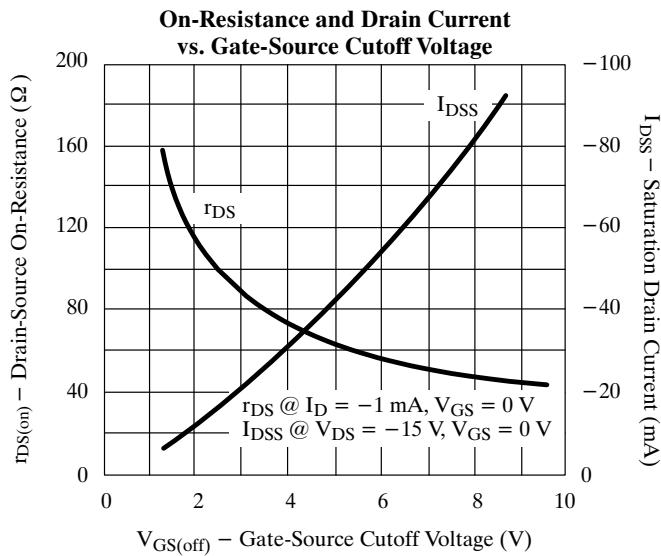
a. T_A = 25°C unless otherwise noted.

PSCIA

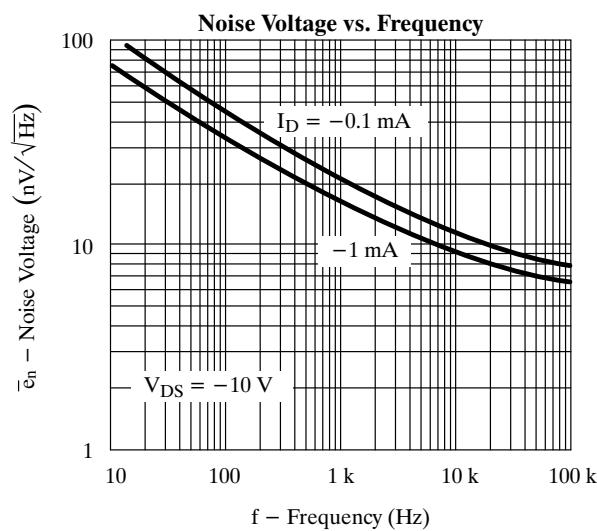
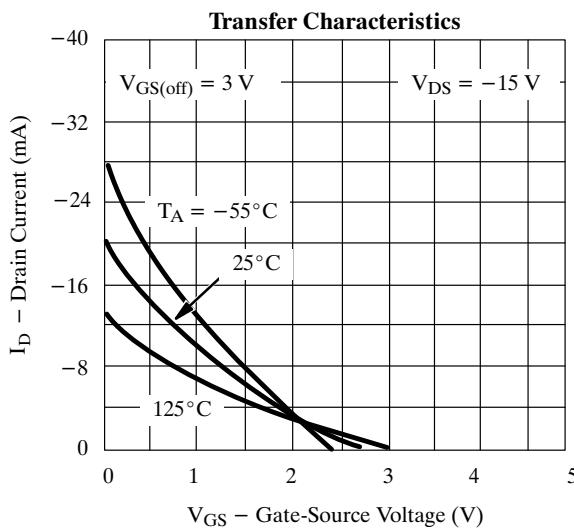
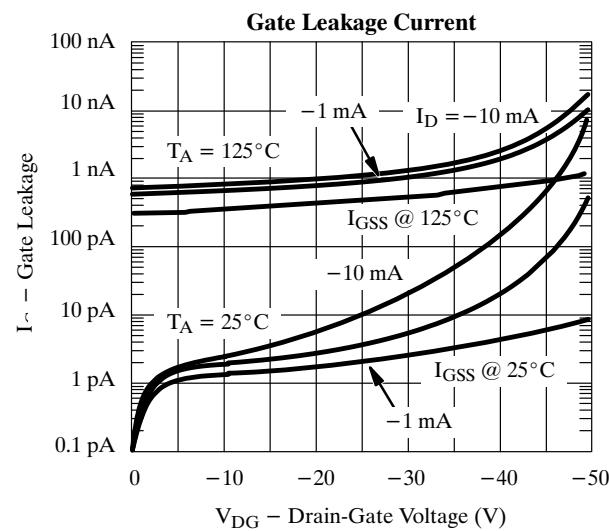
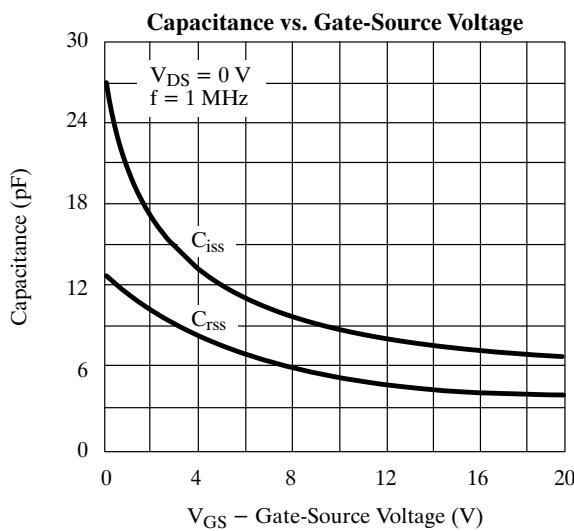
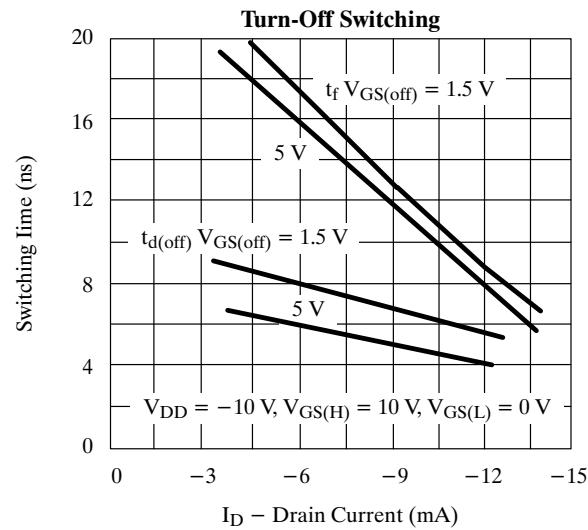
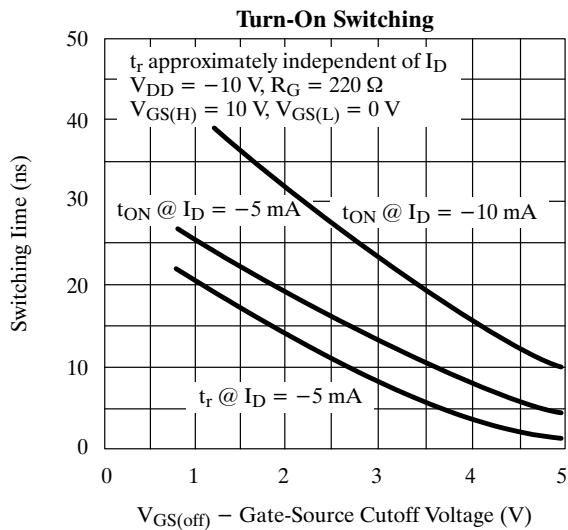
b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

c. Pulse test: PW ≤ 300 μs duty cycle 3%.

Typical Characteristics



Typical Characteristics (Cont'd)



Switching Time Test Circuit

	P1086	P1087
V _{DD}	-6 V	-6 V
V _{GG}	20 V	12 V
R _L *	910 Ω	1800 Ω
R _G *	100 Ω	220 Ω
I _{D(on)}	-15 mA	-3 mA

*Non-inductive

Input Pulse

Rise Time < 1 ns
Fall Time < 1 ns
Pulse Width 100 ns
PRF 1 MHz

Sampling Scope

Rise Time 0.4 ns
Input Resistance 10 MΩ
Input Capacitance 1.5 pF

